

JST08H-800B 8A TRIAC

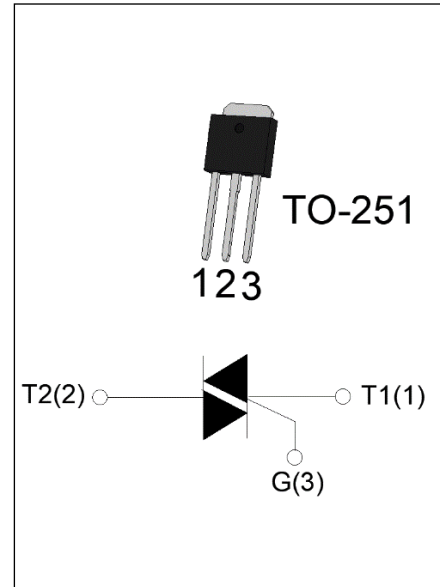
Rev.A.1.0

DESCRIPTION:

The JST08H-800B triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-251 is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ I/II/III/IV}$	50/50/50/70	mA


ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	°C
Operating junction temperature range		T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)		V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)		V_{RRM}	800	V
RMS on-state current ($T_c \leq 91^\circ\text{C}$)		$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)		I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)			88	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)		I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	I - II	di/dt	100	$\text{A}/\mu\text{s}$
	III-IV		50	
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)		I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)		$P_{G(AV)}$	0.5	W
Peak gate power		P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive,off-state;FIG.7)		V_{PP}	1.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	50	mA
		IV		70	
V_{GT}		ALL	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III - IV	MAX.	50	mA
		II		100	
I_H	$I_T=200\text{mA}$		MAX.	60	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	1000	$\text{V}/\mu\text{s}$
$(dV/dt)_c$	$(dI/dt)_c=3.5\text{A}/\text{ms}$, $T_j=125^\circ\text{C}$		MIN.	12	$\text{V}/\mu\text{s}$
t_{on}	$I_G=80\text{mA}$ $I_A=400\text{mA}$ $I_R=40\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	5	μs
t_{off}				30	

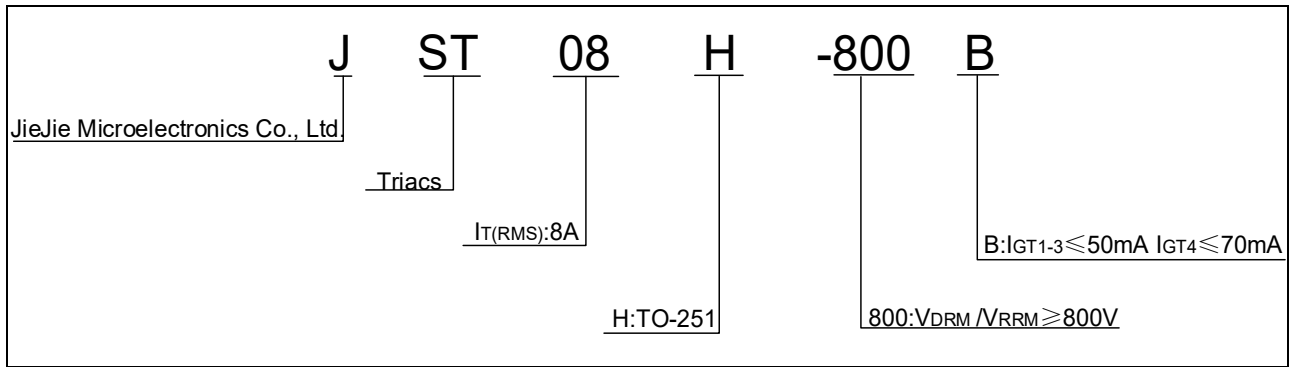
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=11\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.8	V
R_D	Dynamic resistance	$T_j=125^\circ\text{C}$	44	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	0.35	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	3	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	100	$^\circ\text{C}/\text{W}$

ORDERING INFORMATION



MARKING

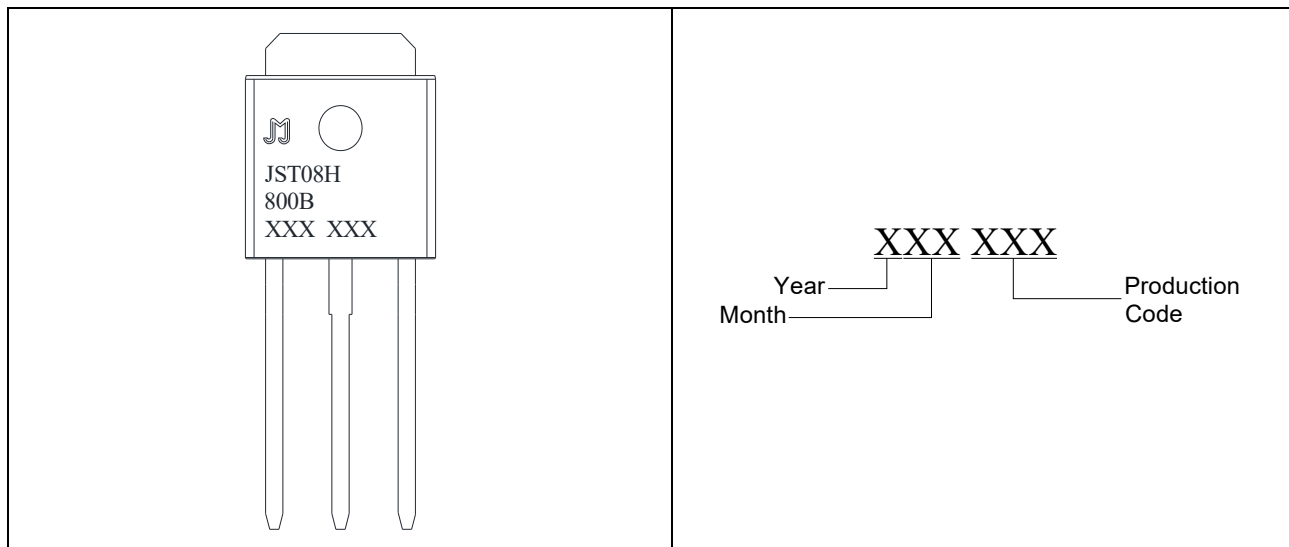


FIG.1 Maximum power dissipation versus RMS on-state current

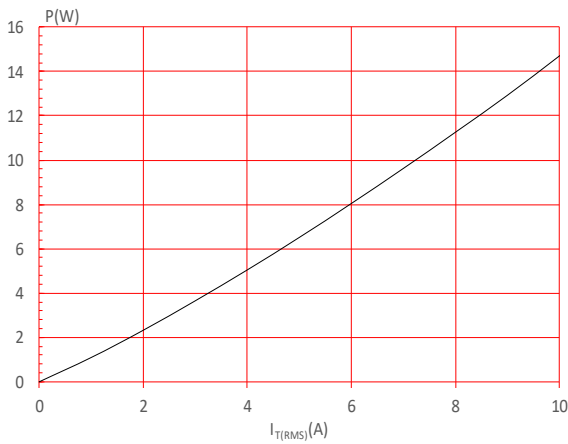


FIG.2: RMS on-state current versus case temperature

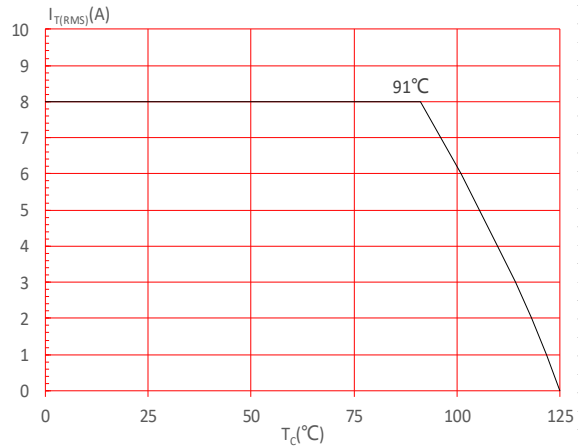


FIG.3: Surge peak on-state current versus number of cycles

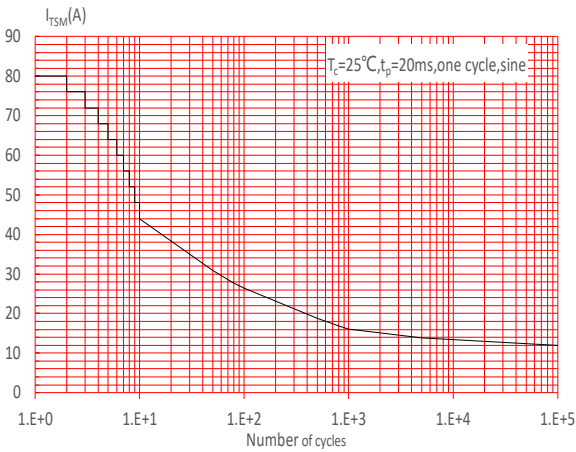


FIG.4: On-state characteristics

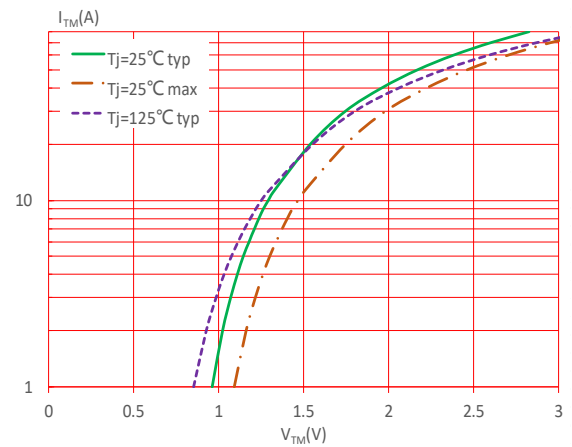


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II: $di/dt < 100\text{A}/\mu\text{s}$; III-IV: $di/dt < 50\text{A}/\mu\text{s}$)

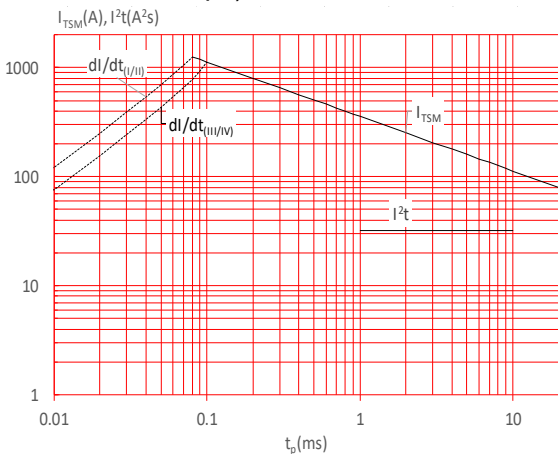


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

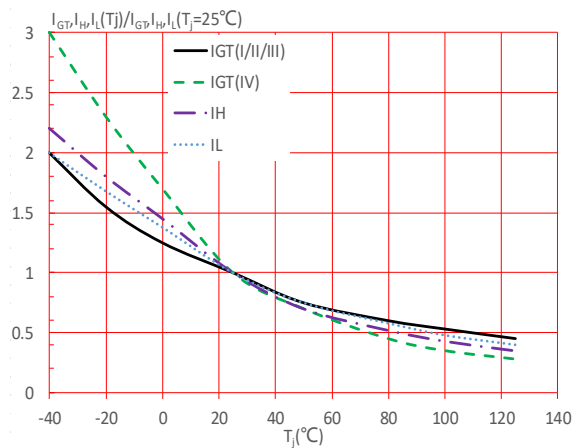
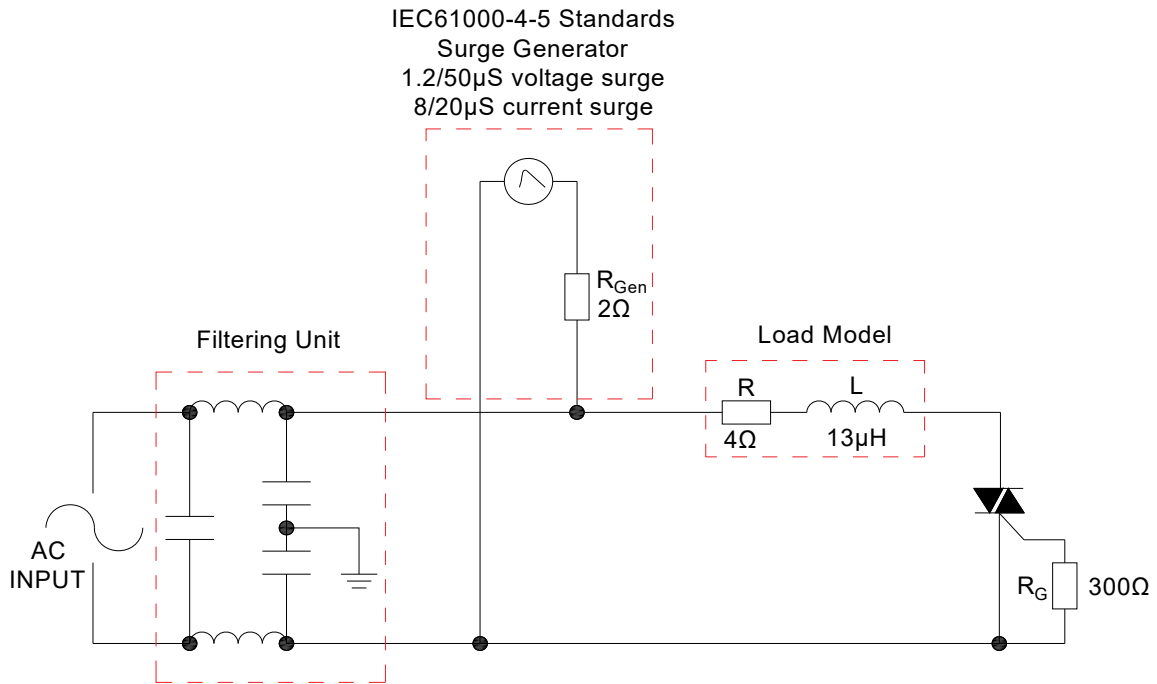


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

ORDERING INFORMATION

Order code	Voltage V _{DRM} /V _{RPM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I -II-III	IV			
JST08H-800B	800	50	70	TO-251	80	Tube

Document Revision History

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

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